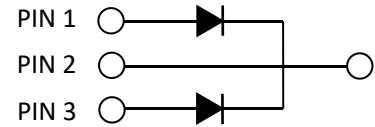


N0D20065D

Silicon Carbide Schottky Diode



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{RSM}	Surge Peak Reverse Voltage	650	V		
V_{DC}	DC Blocking Voltage	650	V		
I_F	Continuous Forward Current	30* 15* 10*	A	$T_C=25^\circ\text{C}$ $T_C=125^\circ\text{C}$ $T_C=140^\circ\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	70*	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Wave	Fig. 7
I_{FSM}	Non-Repetitive Peak Forward Surge Current	90*	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Wave	
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	800*	A	$T_C=25^\circ\text{C}$, $t_p=10$ μs , Pulse	
P_{tot}	Power Dissipation	150* 64*	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	Fig. 6
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

*Per Leg, ** Per Device

Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.0	1.8 2.5	V	$I_F = 10$ A $T_J=25^\circ\text{C}$ $I_F = 10$ A $T_J=175^\circ\text{C}$	Fig. 1
I_R	Reverse Current	1 10	5 30	μA	$V_R = 650$ V $T_J=25^\circ\text{C}$ $V_R = 650$ V $T_J=175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	33		nC	$V_R = 400$ V, $I_F = 10$ A $T_J = 25^\circ\text{C}$: $Q_C = \int_0^{V_R} C(V)dV$	Fig. 4
C	Total Capacitance	514 54 45		pF	$V_R = 0$ V, $T_J = 25^\circ\text{C}$, $f = 1$ MHz $V_R = 200$ V, $T_J = 25^\circ\text{C}$, $f = 1$ MHz $V_R = 400$ V, $T_J = 25^\circ\text{C}$, $f = 1$ MHz	Fig. 3
E_C	Capacitance Stored Energy	6.5		μJ	$V_R = 400$ V	Fig. 5

Thermal Characteristics (Per Leg)

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.99	$^\circ\text{C}/\text{W}$	Fig. 8

Typical Performance(Per Leg)

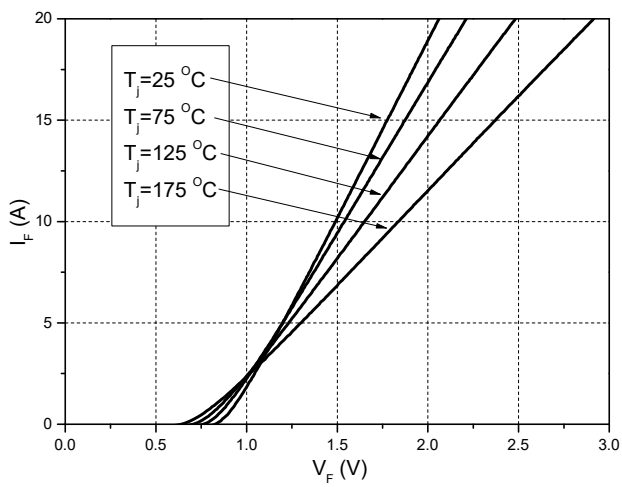


Figure 1. Forward Characteristics

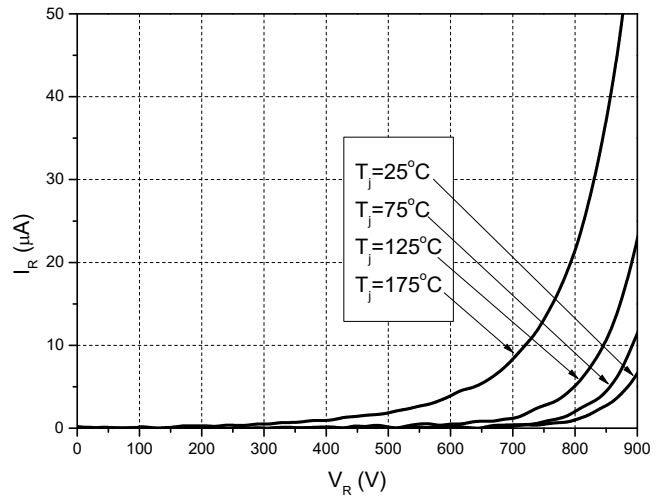


Figure 2. Reverse Characteristics

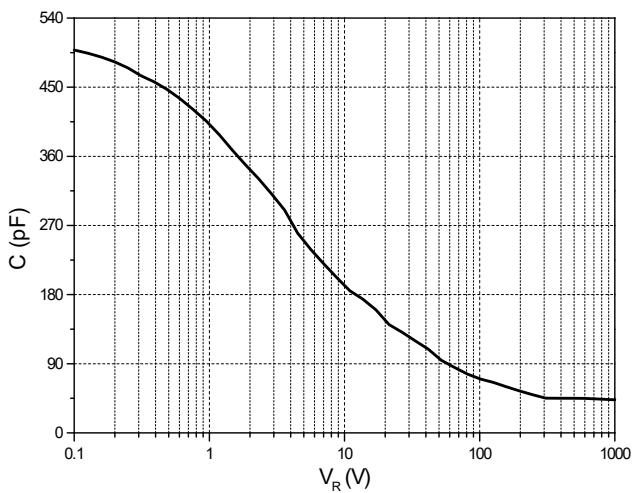


Figure 3. Capacitance vs. Reverse Voltage

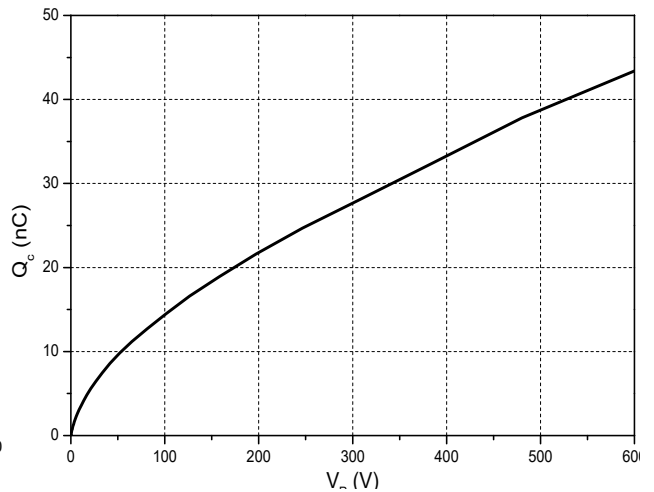


Figure 4. Total Capacitance Charge vs. Reverse Voltage

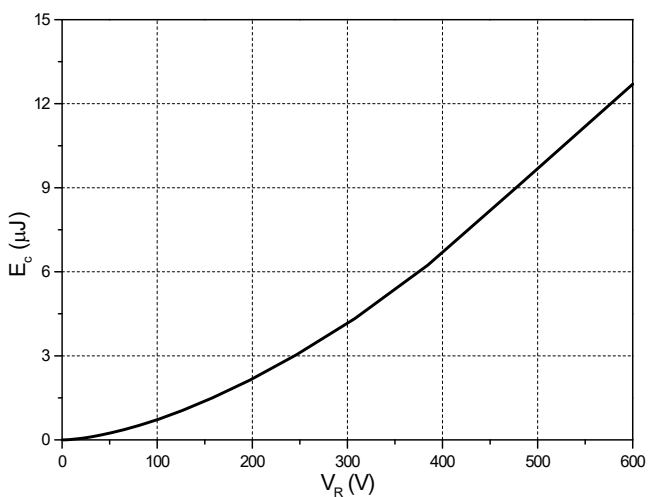


Figure 5. Capacitance Stored Energy

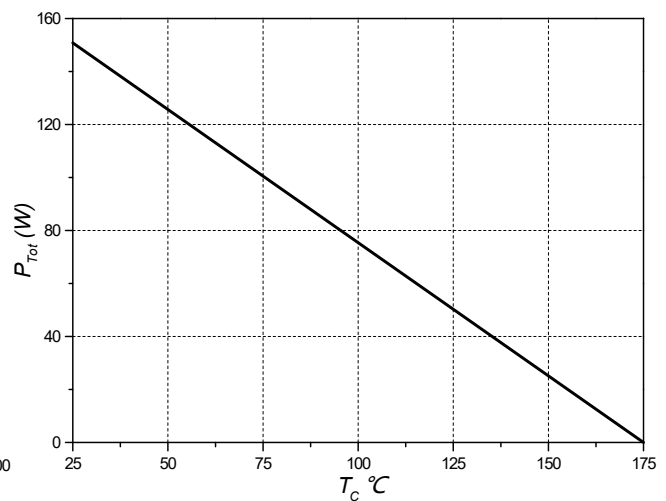


Figure 6. Power Derating

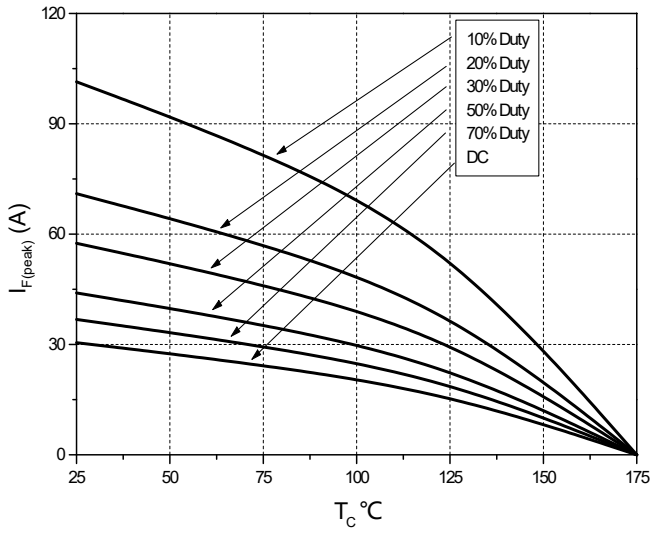


Figure 7. Current Derating

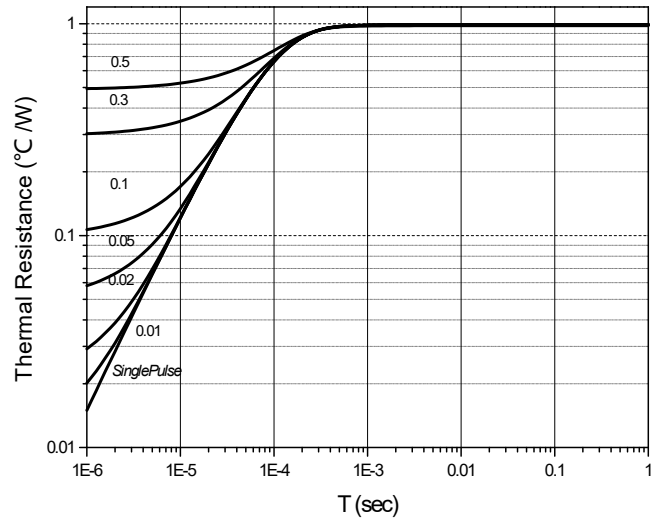
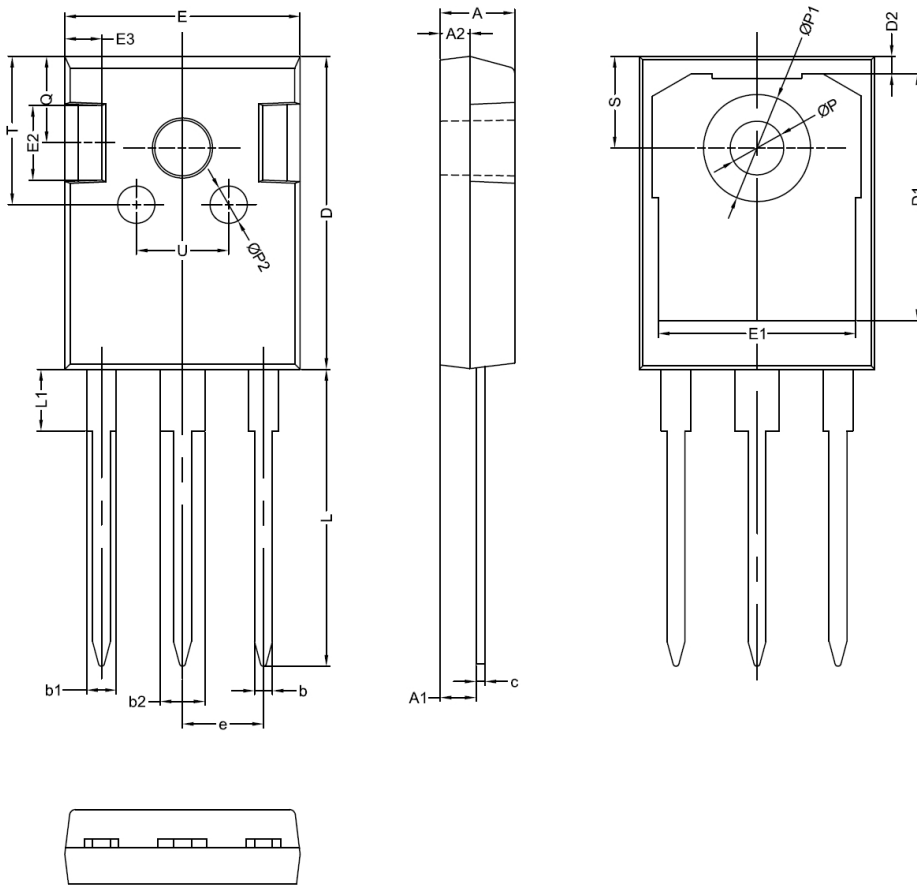


Figure 8. Transient Thermal Impedance

Package Dimensions: TO-247-3L



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
b2		3.00	
c	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.55	
D2		1.20	
E	15.60	15.80	16.0
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	-	-	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	